

Docket No. 5230

IN THE CLAIMS

A clean copy of the amended claims is set forth below.

1 (Amended). A method of reducing notching in etched anisotropic openings in silicon over an insulator layer comprising

A2 anisotropically etching openings in silicon with a sulfur hexafluoride etchant in a plasma etch chamber fitted with a powered substrate support while pulsed bias power is applied to the substrate support electrode during the etch step.

A3 4 (Amended). A method according to claim 2 wherein the pulsed bias power is applied at a duty cycle of 10% to 80% using a 6 microsecond period.

[Add the following claims:]

A4 --10. A method according to claim 6 wherein no bias power is used during the deposition step.

11. A method according to claim 6 wherein etching is carried out in the absence of oxygen.

12. A method according to claim 7 wherein pulsed bias power is applied during the overetch step.

13. A method according to claim 6 wherein pulsed bias power is used during the overetch step.--

Cancel claim 3.